

# N-channel TrenchMOS logic level FET Rev. 2 — 21 April 2011

Product data sheet

#### **Product profile** 1.

### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 1.2 Features and benefits

AEC Q101 compliant

Low conduction losses due to low on-state resistance

### **1.3 Applications**

Automotive and general purpose power switching

### 1.4 Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	55	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C	-	-	34	А
P <sub>tot</sub>	total power dissipation		-	-	85	W
Static chara	acteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	24	32	mΩ
		$\label{eq:VGS} \begin{array}{l} V_{GS} = 5 \ V; \ I_{D} = 25 \ A; \\ T_{j} = 25 \ ^{\circ}C \end{array}$	-	26	35	mΩ
Avalanche I	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{array}{l} {I_{D}}=14 \; A;  V_{sup} \leq 25 \; V; \\ {R_{GS}}=50 \; \Omega;  V_{GS}=5 \; V; \\ {T_{j(\text{init})}}=25 \; ^{\circ}\text{C}; \\ \text{unclamped} \end{array}$	-	-	49	mJ



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### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

### 3. Ordering information

Table 3.         Ordering information					
Type number	Package				
	Name	Description	Version		
BUK9635-55A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404		

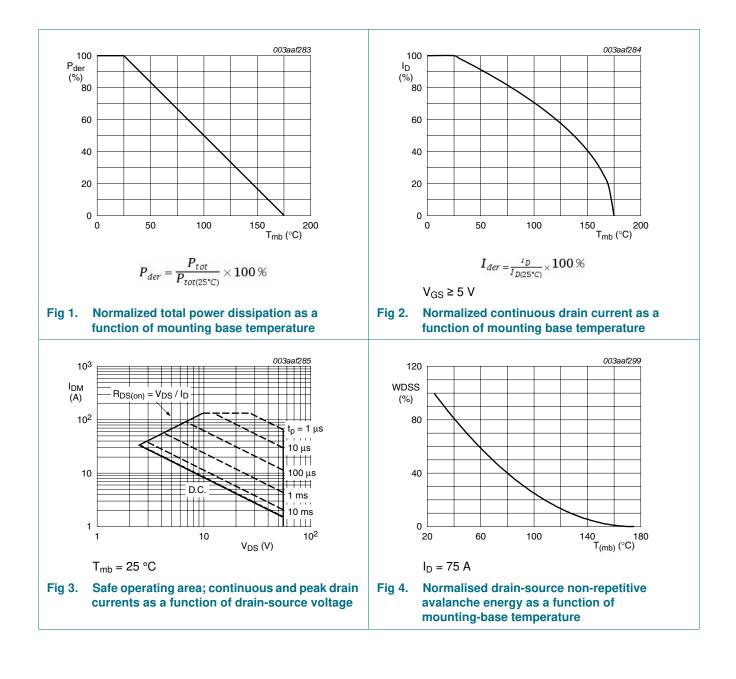
### 4. Limiting values

### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

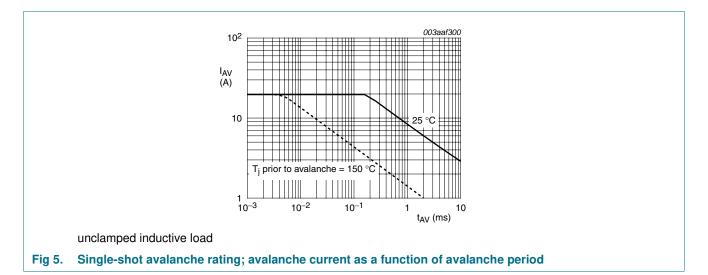
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	55	V
V <sub>DGR</sub>	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	55	V
V <sub>GS</sub>	gate-source voltage		-10	10	V
I <sub>D</sub>	drain current	$T_{mb} = 100 \ ^{\circ}C$	-	24	А
		T <sub>mb</sub> = 25 °C	-	34	А
I <sub>DM</sub>	peak drain current	T <sub>mb</sub> = 25 °C; pulsed	-	133	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C	-	85	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
V <sub>GSM</sub>	peak gate-source voltage	pulsed; t <sub>p</sub> ≤ 50 μs	-15	15	V
Source-drai	in diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	34	А
I <sub>SM</sub>	peak source current	pulsed; T <sub>mb</sub> = 25 °C	-	133	А
Avalanche I	ruggedness				
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{array}{l} I_D = 14 \text{ A}; \ V_{sup} \leq 25 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} = 5 \text{ V}; \ T_{j(\text{init})} = 25 \ ^{\circ}\text{C}; \ \text{unclamped} \end{array}$	-	49	mJ

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# BUK9635-55A

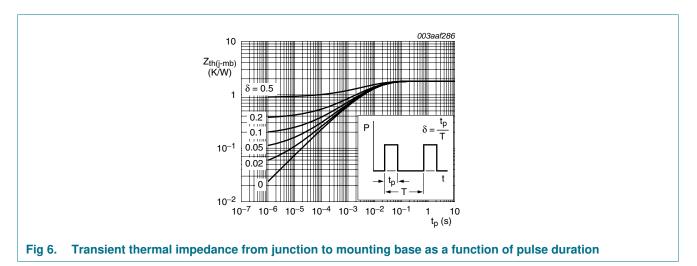
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### 5. Thermal characteristics

#### Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	1.8	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint; FR4 board	-	50	-	K/W



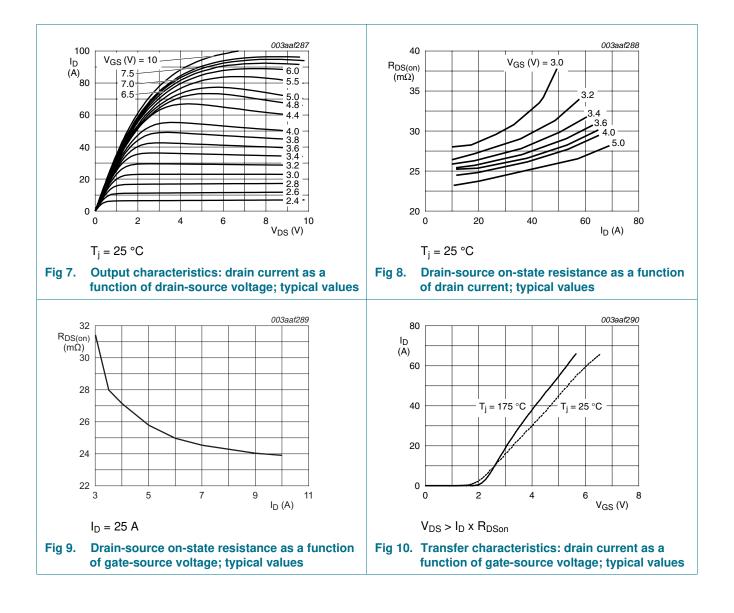
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### 6. Characteristics

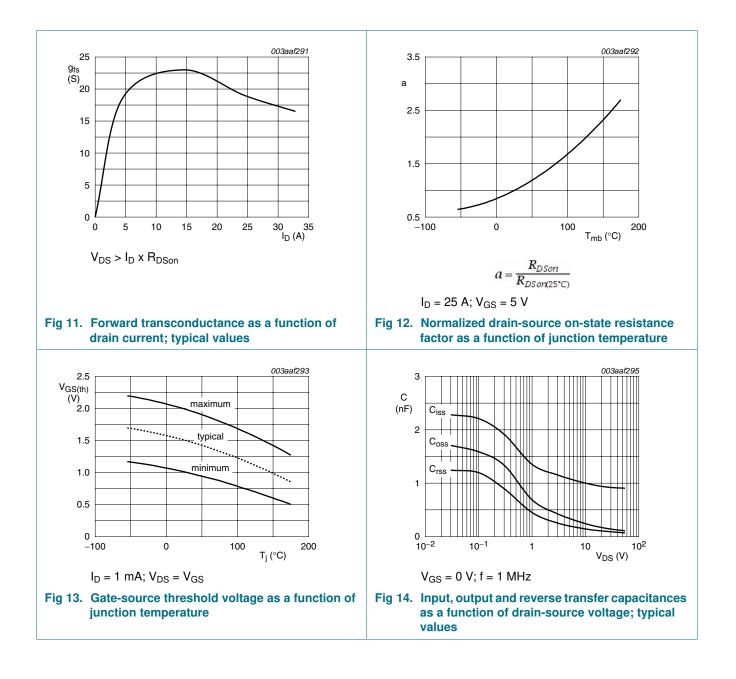
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara				<b>7</b> 1-	-	
V <sub>(BR)DSS</sub> drain-source		I <sub>D</sub> = 0.25 mA; V <sub>GS</sub> = 0 mV; T <sub>i</sub> = 25 °C	55	-	-	V
(21)200	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ mV}; T_i = -55 \text{ °C}$	50	-	-	V
V <sub>GS(th)</sub>	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_i = -55 \text{ °C}$	-	-	2.3	V
voltage	voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>i</sub> = 25 °C	1	1.5	2	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C	0.5	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
		V <sub>DS</sub> = 55 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
	V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA	
R <sub>DSon</sub> drain-source on-sta resistance	drain-source on-state	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	26.5	38	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	24	32	mΩ
		$V_{GS}$ = 5 V; $I_D$ = 25 A; $T_j$ = 175 °C	-	-	70	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	26	35	mΩ
Dynamic ch	aracteristics					
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	880	1173	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \ ^{\circ}C$	-	165	198	pF
C <sub>rss</sub>	reverse transfer capacitance		-	111	152	pF
d(on)	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$	-	6	9	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	36	55	ns
d(off)	turn-off delay time		-	96	134	ns
t <sub>f</sub>	fall time		-	73	102	ns
L <sub>D</sub>	internal drain inductance	from upper edge of drain mounting base to centre of die; T <sub>j</sub> = 25 °C	-	2.5	-	nH
		from drain lead 6 mm from package to centre of die; T <sub>j</sub> = 25 °C	-	4.5	-	nH
-S	internal source inductance	from source lead to source bond pad; $T_i = 25 \text{ °C}$	-	7.5	-	nH
Source-dra	in diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.85	1.2	V
		I <sub>S</sub> = 34 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	1.1	-	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 34 A; dI <sub>S</sub> /dt = -100 A/μs;	-	36	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	0.07	-	μC

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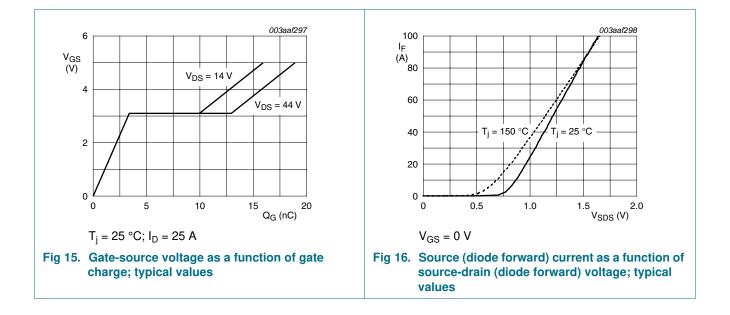
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### 7. Package outline

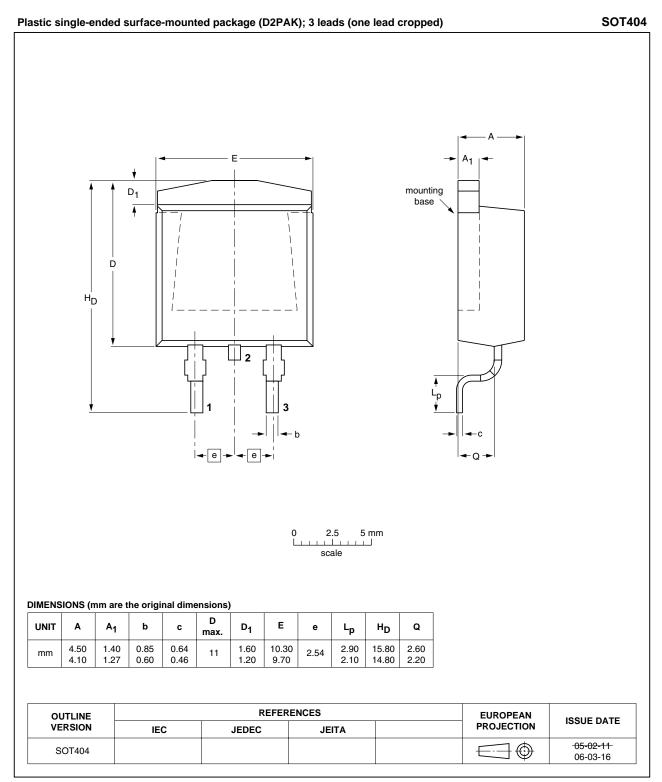


Fig 17. Package outline SOT404 (D2PAK)

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### 8. Revision history

Table 7. Revision hi	story				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
BUK9635-55A v.2	20110421	Product data sheet	-	BUK9535_9635-55A_1	
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> </ul>				
	<ul> <li>Legal texts have be</li> </ul>	een adapted to the new c	ompany name where app	propriate.	
	<ul> <li>Type number BUK</li> </ul>	9635-55A separated from	n data sheet BUK9535_90	635-55A_1.	
BUK9535_9635-55A_1	20000201	Product specification	-	-	

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### 9. Legal information

### 9.1 Data sheet status

Document status [1] [2]	Product status 3	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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